

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB50-28F is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.5 A
V_{CB0}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	75W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.3 °C/W

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10728

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA			35			V
BV_{CES}	I _C = 200 mA			65			V
BV_{EBO}	I _E = 10 mA			4.0			V
I_{CB0}	V _{CB} = 30 V					2.0	mA
I_{CES}	V _{CE} = 30 V $T_C = 125\text{ }^\circ\text{C}$					10	mA
h_{FE}	V _{CE} = 5.0 V	I _C = 500 mA		5.0		---	---
C_{ob}	V _{CB} = 28 V	f = 1.0 MHz				80	pF
f_T	V _{CE} = 10 V	I _C = 500 mA	f = 100 MHz	200			MHz
P_G	V _{CE} = 28 V	P _{OUT} = 50 W		6.0			dB
η_C			f = 175 MHz		60		%